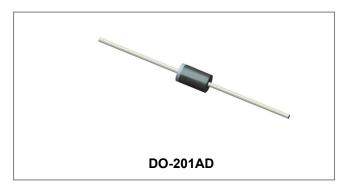


#### Technical Data Data Sheet N0887, Rev. A





# **SB10200 SCHOTTKY RECTIFIER**



## **Features**

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

# **Circuit Diagram**



# **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Disk drives
- Battery charging

## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	200	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @T <sub>A</sub> =75°C, rectangular wave form	10	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse, T <sub>C</sub> =25°C	200	Α

## **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	V <sub>F1</sub> @ 10A, Pulse, T <sub>J</sub> = 25 °C		1.10	V
	V <sub>F2</sub>	@ 10A, Pulse, T <sub>J</sub> = 125 °C	-	0.90	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = Rated V <sub>R</sub> , Pulse, T <sub>J</sub> = 25 °C	-	1	mA
	I <sub>R2</sub>	@V <sub>R</sub> = Rated V <sub>R</sub> , Pulse, T <sub>J</sub> = 125 °C	-	7.0	mA
Series Inductance	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com
    sales@ smc-diodes.com



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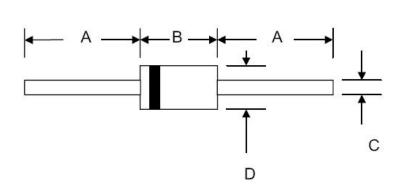




# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	DC operation	10	°C/W
Approximate Weight	wt	-	1.02	g

## **Mechanical Dimensions DO-201AD**



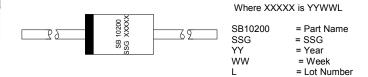
SYMBOL	Millimeters		Inches		
STMBOL	Min.	Max.	Min.	Max.	
Α	25.4	-	1.000	-	
В	8.50	9.50	0.335	0.374	
С	1.2	1.3	0.048	0.052	
D	5.0	5.6	0.197	0.220	

# **Ordering Information**

Device	Package	Shipping	
SB10200	DO-201AD	1250pcs / tape	
3610200	(Pb-Free)	1250pcs / tape	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**



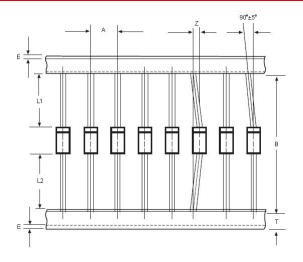


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## **Carrier Tape Specification DO-201AD**



SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
Α	9.50	10.50	
В	50.9	53.9	
Z	-	1.20	
Т	5.60	6.40	
Е	-	0.80	
IL1-L2I	-	1.0	

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